

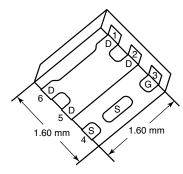
HALOGEN FREE



P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)						
	0.058 at $V_{GS} = -4.5 \text{ V}$	- 9 ^a							
- 20	0.077 at V _{GS} = - 2.5 V	- 9 ^a	7.6 nC						
	0.105 at V _{GS} = - 1.8 V	- 5							

PowerPAK SC-75-6L-Single



Ordering Information:

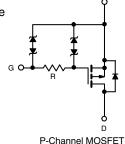
SiB433EDK-T1-GE3 (Lead (Pb)-free and Halogen-free)

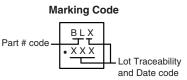
FEATURES

- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-75 Package
 - Small Footprint Area
 - Low On-Resistance
- 100 % $\rm R_{\rm g}$ Tested Typical ESD Performance 2000 V
- Built in ESD Protection with Zener Diode
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Load Switch for Portable Devices
- Charger Switch for Portable **Devices**





ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unle	ess otherwise no	oted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	- 20	V	
Gate-Source Voltage		V_{GS}	± 8	V	
	T _C = 25 °C		- 9 ^a		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	I-	- 9 ^a		
Continuous Diain Current (1) = 150 C)	T _A = 25 °C	I _D	- 5.3 ^{b, c}		
	T _A = 70 °C		- 4.3 ^{b, c}	Α	
Pulsed Drain Current		I _{DM}	- 20		
Continuous Source-Drain Diode Current	T _C = 25 °C	l _a	- 9 ^a		
Continuous Cource-Drain Diode Current	T _A = 25 °C	I _S	- 2 ^{b, c}		
	T _C = 25 °C		13		
Maximum Power Dissipation	T _C = 70 °C	P _D	8.4	w	
Maximum Fower Dissipation	T _A = 25 °C	LD	2.4 ^{b, c}	1 vv	
	T _A = 70 °C		1.6 ^{b, c}		
Operating Junction and Storage Temperature Ra	inge	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature	e) ^{d, e}		260]	

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	41	51	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	7.5	9.5]				

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 105 °C/W.

Document Number: 65652 S12-0979-Rev. B, 30-Apr-12

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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V			
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 13		14/00			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1 _D = - 250 μΑ		2.5		mV/°C			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.4		- 1	V			
Cata Carriaga I aglicana	ı	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 6	μΑ			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 0.5				
Zana Oata Wallana Busin Ourmant		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1				
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 55 °C			- 10	1			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 15			Α			
		V _{GS} = - 4.5 V, I _D = - 3.7 A		0.047	0.058				
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 3.2 A		0.064	0.077	Ω			
	-(- /	V _{GS} = - 1.8 V, I _D = - 1.5 A		0.085	0.105	1			
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 3.7 A		12		S			
Dynamic ^b				l					
•	_	V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 5.3 A		14	21	nC			
Total Gate Charge	Q_g	20 00 2		7.6	12				
Gate-Source Charge	Q _{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -5.3 \text{ A}$		0.8					
Gate-Drain Charge	Q _{gd}			3.1					
Gate Resistance	R_{g}	f = 1 MHz	0.4	2	4	kΩ			
Turn-On Delay Time	t _{d(on)}			0.2	0.3				
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_{L} = 2.3 \Omega$		1	1.5				
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -4.3 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		4	6				
Fall Time	t _f			2	3				
Turn-On Delay Time	t _{d(on)}			0.09	0.14	μs			
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_{L} = 2.3 \Omega$		0.4	0.6				
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -4.3 \text{ A}, V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$		5.2	7.8	1			
Fall Time	t _f			2.3	3.5	1			
Drain-Source Body Diode Characterist	ics			l	L	1			
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 9				
Pulse Diode Forward Current	I _{SM}				- 20	Α			
Body Diode Voltage	V_{SD}	I _S = - 4.3 A, V _{GS} = 0 V		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time t _{rr}				30	60	ns			
Body Diode Reverse Recovery Charge	Q _{rr}	_ 43 A dl/dt = 100 A/vo T = 25 °C		20	40	nC			
Reverse Recovery Fall Time	t _a	$I_F = -4.3 \text{ A, dI/dt} = 100 \text{ A/}\mu\text{s, T}_J = 25 ^{\circ}\text{C}$		13					
Reverse Recovery Rise Time	t _b			17		ns			

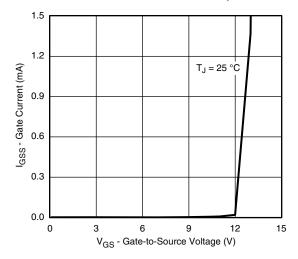
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

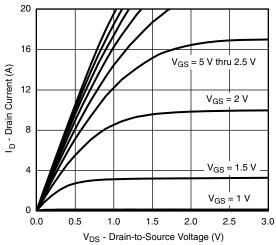
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



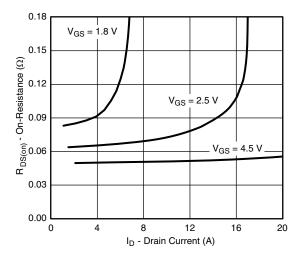
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



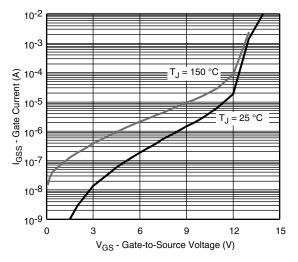
Gate Current vs. Gate-Source Voltage



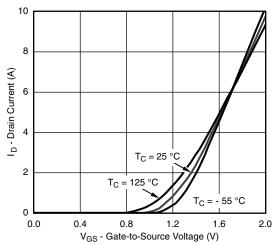
Output Characteristics



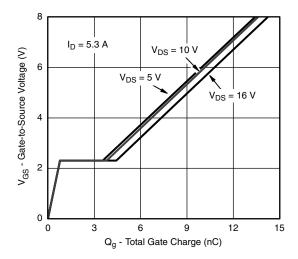
On-Resistance vs. Drain Current



Gate Current vs. Gate-Source Voltage



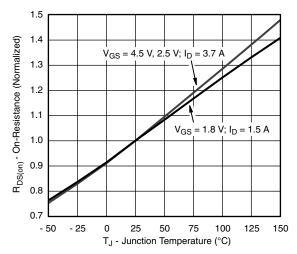
Transfer Characteristics



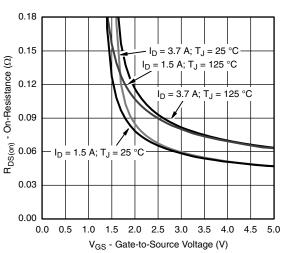
Gate Charge

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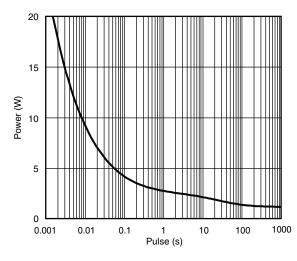
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



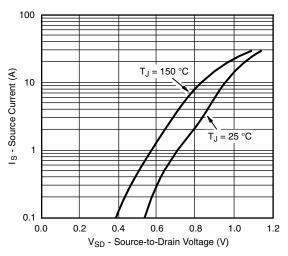
On-Resistance vs. Junction Temperature



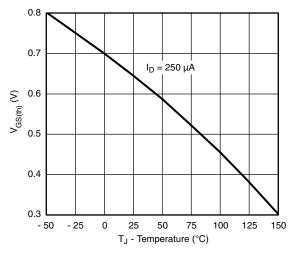
On-Resistance vs. Gate-to-Source Voltage



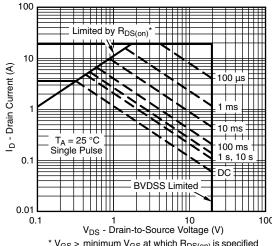
Single Pulse Power, Junction-to-Ambient



Soure-Drain Diode Forward Voltage



Threshold Voltage



* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

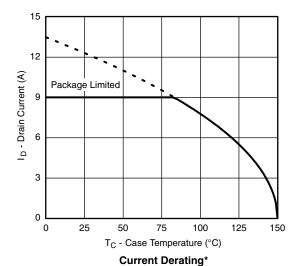
Safe Operating Area, Junction-to-Ambient

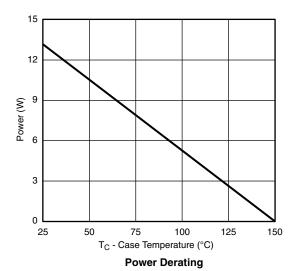






TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

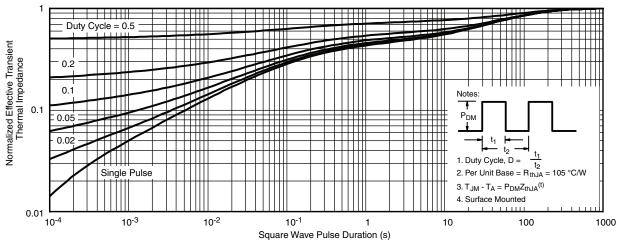




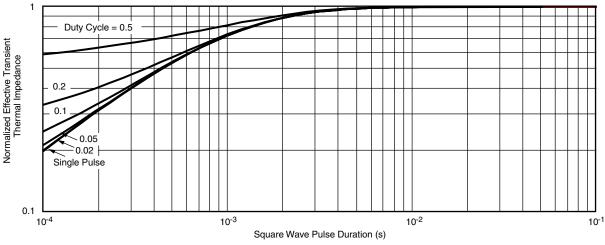
 $^{^*}$ The power dissipation P_D is based on $T_{J(max)}$ = 150 $^{\circ}$ C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



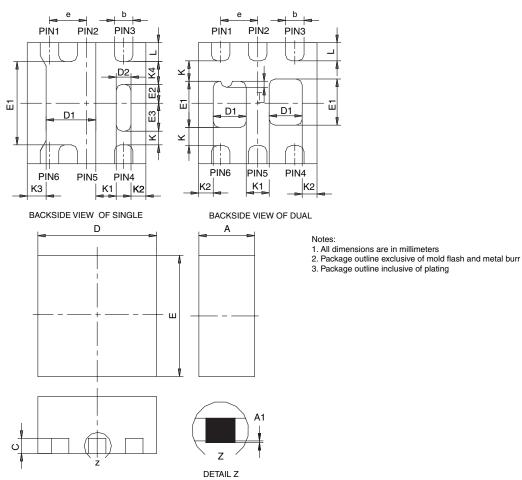
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/ tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65652.





PowerPAK® SC75-6L



			SINGL			DUAL PAD						
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						
E3	0.32	0.37	0.42	0.013	0.015	0.017						
е		0.50 BSC 0.020 BSC		0.50 BSC			0.020 BSC					
K	0.180 TYP			0.007 TYP		0.245 TYP 0.0		0.010 TYP).010 TYP			
K1	0.275 TYP				0.011 TYP		0.320 TYP 0.013 TYP					
K2	0.200 TYP				0.008 TYP		0.200 BSC 0.008 T			0.008 TYP		
К3	0.255 TYP				0.010 TYP							
K4	0.300 TYP				0.012 TYP							
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
T							0.03	0.08	0.13	0.001	0.003	0.005

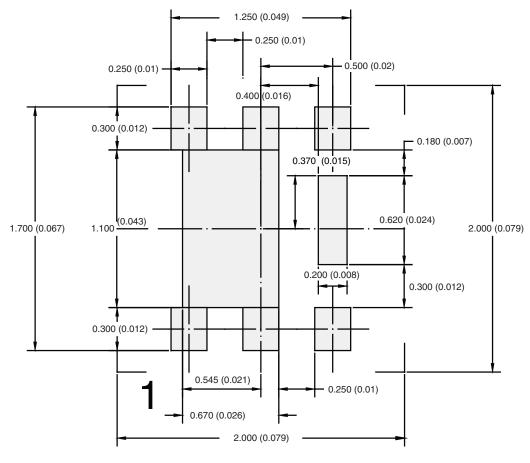
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5935

Document Number: 73000 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICATION NOT



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